

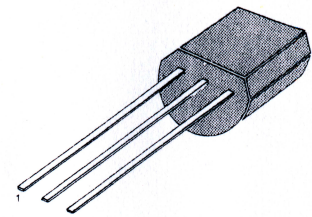
△SWITCHING AND AMPLIFIER APPLICATIONS

- Suitable for automatic insertion in thick and thin-film circuits
- Complement to BC847

△ABSOLUTE MAXIMUM RATINGS (TA=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	V _{CES}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current (DC)	I _C	-100	mA
Collector Dissipation	P _C	310	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55-150	°C

T0-92



1. Collector 2. Base 3. Emitter

△ELECTRICAL CHARACTERISTICS (TA=25°C)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Emitter Breakdown Voltage	BV _{CEO}	I _C =-10mA, I _B =0	-45			V
Collector Emitter Breakdown Voltage	BV _{CBO}	I _C =-0.1mA, I _B =0	-50			V
Emitter Base Breakdown Voltage	BV _{EBO}	I _E =-0.1mA, I _C =0	-5			V
Collector Cut-off Current	I _{CBO}	V _{CB} =-30V, I _B =0			-15	nA
DC Current Gain	HFE1	V _{CE} =-5V, I _C =-2mA	110		800	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =-10mA, I _B =-0.5mA		-90	-300	mV
	V _{CE(sat)}	I _C =-100mA, I _B =-5mA		-250	-650	mV
Base Emitter Saturation Voltage	V _{BE(sat)}	I _C =-10mA, I _B =-0.5mA		-700		mV
	V _{BE(sat)}	I _C =-100mA, I _B =-5mA		-900		mV
Base Emitter On Voltage	V _{BE(on)}	V _{CE} =-5V, I _C =-2mA	-600	-660	-750	mV
	V _{BE(on)}	V _{CE} =-5V, I _C =-10mA			-800	mV
Current Gain Bandwidth Product	f _T	V _{CE} =-5V, I _C =-10mA, f=100MHz		150		MHz
Output Capacitance	C _{ob}	V _{CB} =-10V, f=1MHz, I _E =0			6	pF
Noise Figure	NF	V _{CE} =-5V, I _C =-200μA, f=1KHz, R _G =2KΩ		2	10	dB